

INF-119

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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| In re the Application of:<br><br>GRIT SCHWALBE ET AL.<br><br>Serial No.: NEW APPLICATION<br><br>Filed: December 1, 2003<br><br>For: METHOD FOR PATTERNING<br>DIELECTRIC LAYERS ON<br>SEMICONDUCTOR SUBSTRATES | <br><br><br><br>Art Unit: Unknown<br><br>Examiner: Not Yet Assigned |
|---|---|

INFORMATION DISCLOSURE STATEMENT ACCOMPANYING FILING

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Applicants wish to make of record in the above-identified application the document or documents referenced on the attached Form PTO-1449. A copy of each reference is enclosed herewith.

The cited references are mentioned in the German Office Action (copy enclosed) of applicant's corresponding German patent application and are believed relevant for at least that reason.

It is respectfully requested that the information be expressly considered during the prosecution of this application, and that each reference be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

Inventor: Grit SCHWALBE et al.  
Serial No. New Application  
Art Unit: Unknown

Attorney Docket No. INF-119  
Page 2

This submission does not represent that any referenced document is material or constitutes "prior art." If it should be determined that one or more of the referenced documents constitute "prior art" under United States law, Applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of the reference or references.

Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over any referenced document, should it be applied against the claims of the present application.

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Date: December 1, 2003

Respectfully submitted,

GRIT SCHWALBE ET AL.

By:



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Registration No. 42,956

|  |  |   |          |                                   |       |                                      |                               |
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| <b>INFORMATION DISCLOSURE CITATION</b><br><i>(Use several sheets if necessary)</i> |  |   |          | ATTY DOCKET NO.<br><b>INF-119</b> |       | SERIAL NO.<br><b>New Application</b> |                               |
|  |  |   |          | GRIT SCHWALBE ET AL.              |       |                                      |                               |
|  |  |   |          | FILING<br><b>DECEMBER 1, 2003</b> |       | GROUP<br><b>Unknown</b>              |                               |
| <b>U.S. PATENT DOCUMENTS</b>   |  |   |          |                                   |       |                                      |                               |
| *EXAMINER<br>INITIAL   |  | DOCUMENT NUMBER   | DATE     | NAME                              | CLASS | SUBCLASS                             | FILING DATE<br>IF APPROPRIATE |
|  |  | 5,660,681   | 08/26/97 | FUKUDA ET AL.                     | 438   | 695                                  | 08/19/96                      |
|  |  | 6,232,237   | 05/15/01 | TAMAOKA ET AL.                    | 438   | 725                                  | 12/08/98                      |
|  |  | 6,235,453   | 05/22/01 | YOU ET AL.                        | 430   | 329                                  | 07/07/99                      |
|  |  | 2002/0076935  | 06/20/02 | MAEX ET AL.                       | 438   | 706                                  | 09/28/01                      |
|  |  | 2001/0005635  | 06/28/01 | KITAGAWA                          | 438   | 710                                  | 12/14/00                      |
|  |  | 2002/0146647  | 10/10/02 | AOKI ET AL.                       | 430   | 313                                  | 03/11/02                      |
|  |  | 2002/0164877  | 11/07/02 | CATABAY ET AL.                    | 438   | 694                                  | 05/02/01                      |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
| <b>FOREIGN PATENT DOCUMENTS</b>  |  |   |          |                                   |       |                                      |                               |
|  |  | DOCUMENT NUMBER   | DATE     | COUNTRY                           | CLASS | SUBCLASS                             | TRANSLATION<br>YES      NO    |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
|  |  |   |          |                                   |       |                                      |                               |
| <b>OTHER DOCUMENTS    (Including Author, Title, Date, Pertinent Pages, Etc.)</b>   |  |   |          |                                   |       |                                      |                               |
|  |  | Article entitled "Limitation of HF-Based Chemistry for Deep-Submicron Contact Hole Cleaning on Silicides" by M.R. Baklanov et al. , J. Electrochem. Soc., Vol. 145, No. 9 September 1998 by The Electrochemical Society, Inc., pp 3240-3246.<br>Article entitled "low-k dielectric etching" by D.J. Thomas et al., published March 2001 in Solid State Technology, pages107, 108, 112-116 (www.solid-state.com) |          |                                   |       |                                      |                               |
|  |  | Copy of German Office Action dated October 20, 2003   |          |                                   |       |                                      |                               |
| EXAMINER   |  |   |          | DATE CONSIDERED                   |       |                                      |                               |

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.